

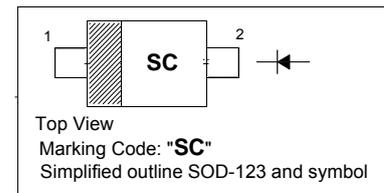
Surface Mount Schottky Barrier Diode

Features

- Very low forward voltage
- High Current Capability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



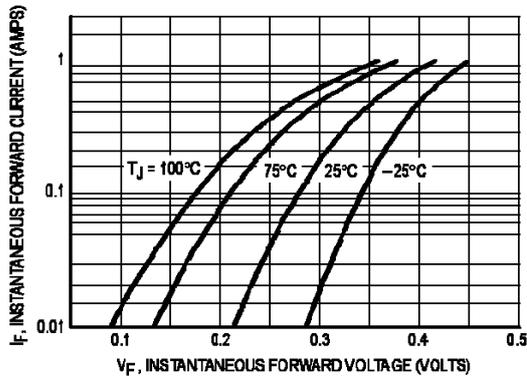
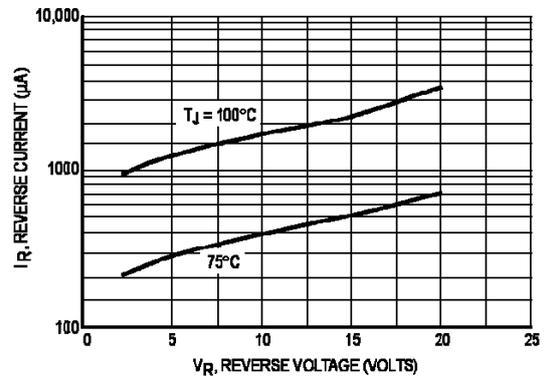
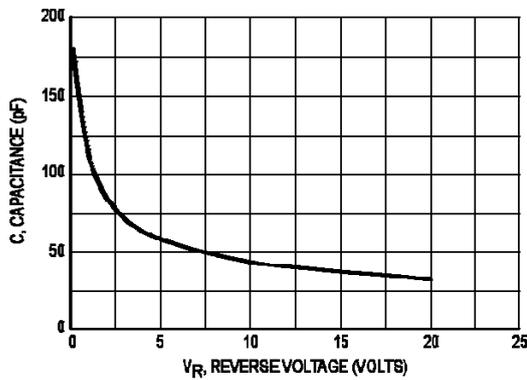
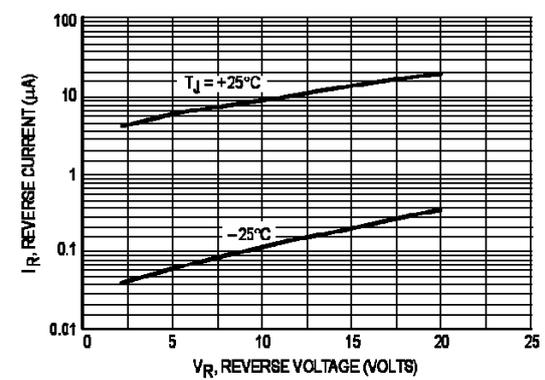
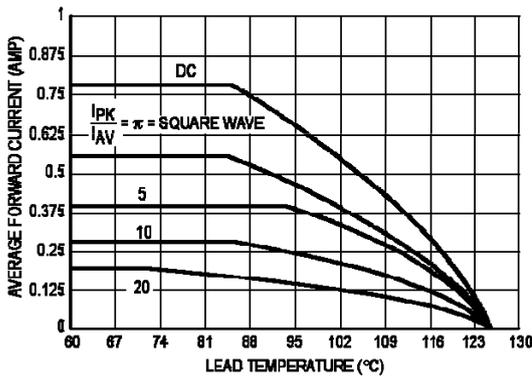
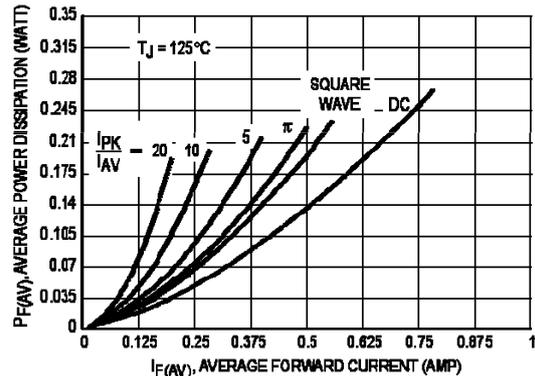
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RRM}	20	V
Working Peak Reverse Voltage	V_{RWM}	20	V
DC Reverse Voltage	V_R	20	V
Average Rectified Forward Current	$I_{F(AV)}$	0.5	A
Non-Repetitive Peak Forward Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	5.5	A
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	340	$^\circ\text{C/W}$
Thermal Resistance Junction to Lead	$R_{\theta JL}$	150	$^\circ\text{C/W}$
Junction Temperature	T_j	- 65 to + 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	- 65 to + 150	$^\circ\text{C}$

¹⁾ Following any rated load condition and with rated V_{RRM} applied.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 0.1\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$ at $I_F = 0.5\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$ at $I_F = 0.1\text{ A}$, $T_j = 100\text{ }^\circ\text{C}$ at $I_F = 0.5\text{ A}$, $T_j = 100\text{ }^\circ\text{C}$	V_F	0.375 0.44 0.26 0.36	V
Reverse Current at $V_R = 10\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ at $V_R = 20\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ at $V_R = 10\text{ V}$, $T_j = 100\text{ }^\circ\text{C}$ at $V_R = 20\text{ V}$, $T_j = 100\text{ }^\circ\text{C}$	I_R	40 150 3 7	μA μA mA mA
Total Capacitance at $V_R = 5\text{ V}$ (test signal range 100 KHz to 1 MHz), $T_j = 25\text{ }^\circ\text{C}$	C_{tot}	110	pF


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

Figure 3. Typical Capacitance

Figure 4. Typical Reverse Current

Figure 5. Current Derating (Lead)

Figure 6. Power Dissipation